

4.0 V to 17 V Input, 3 A Integrated MOSFET Single Synchronous Buck DC/DC Converter

BD9D300MUV

General Description

BD9D300MUV is a synchronous buck switching regulator with built-in low on-resistance power MOSFETs. This integrated circuit (IC) is capable of providing current up to 3 A. It operates high oscillating frequency with low inductance. It has original on-time control system which can operate low power consumption in light load condition. This IC is ideal for reducing standby power consumption of equipment.

Features

- Single Synchronous Buck DC/DC Converter
- **On-time Control**
- Light Load Mode Control
- Over Current Protection (OCP)
- Short Circuit Protection (SCP)
- Thermal Shutdown Protection (TSD)
- Under Voltage Lockout Protection (UVLO)
- Adjustable Soft Start
- Power Good Output
- Over Voltage Protection (OVP)
- VQFN016V3030 Package Backside Heat Dissipation

Applications

- Step-down Power Supply for SoC, FPGA, Microprocessor
- Laptop PC / Tablet PC / Server
- LCD TV
- Storage Device (HDD / SSD)
- 2-series Cell Li-Ion Batteries Equipment
- Printer, OA Equipment
- Distributed Power Supply, Secondary Power Supply

Typical Application Circuit

Key Specifications

- Input Voltage Range: 4 V to 17 V Output Voltage Range: 0.9 V to 5.25 V Output Current: 3 A (Max) Switching Frequency: 1.25 MHz (Typ) High-Side FET ON Resistance: 110 mΩ (Typ) Low-Side FET ON Resistance: 50 mΩ (Typ) Shutdown Current: 3 µA (Typ) 20 µA (Typ)
- **Operating Quiescent Current:**

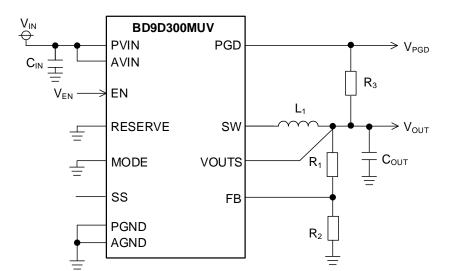
Package

VQFN016V3030

W (Typ) x D (Typ) x H (Max) 3.00 mm x 3.00 mm x 1.00 mm

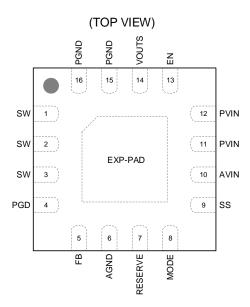


VQFN016V3030



OProduct structure : Silicon integrated circuit OThis product has no designed protection against radioactive rays.

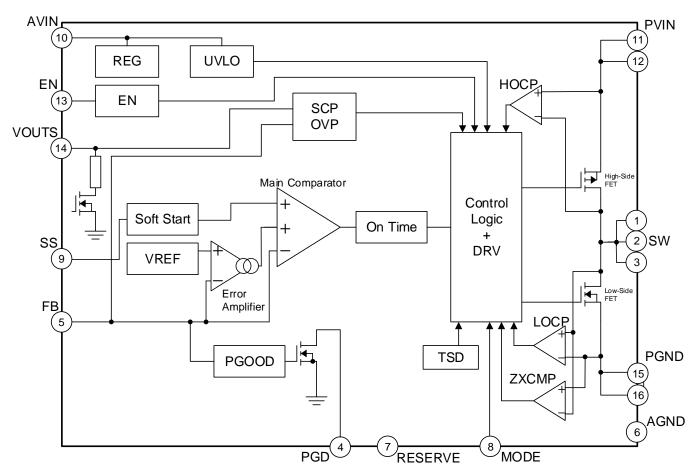
Pin Configuration



Pin Descriptions

| Pin No. | Pin Name | Function |
|---------|----------|--|
| 1, 2, 3 | SW | Switch pin. These pins are connected to the drain of the High-Side and Low-Side FET. In addition, connect an inductor considering the direct current superimposition characteristic. |
| 4 | PGD | Power Good pin. This pin is an open drain output that requires a pull-up resistor (to the VOUTS pin). See <u>page 15</u> for setting the resistance. If not used, this pin can be left floating or connected to Ground. |
| 5 | FB | Output voltage feedback pin. See page 32 for how to calculate the resistances of the output voltage setting. |
| 6 | AGND | Ground pin for the control circuit. |
| 7 | RESERVE | Reserve pin. Connect to Ground. |
| 8 | MODE | Pin for setting switching control mode. Connecting this pin to the VOUTS pin forces the device to operate in the Pulse Width Modulation (PWM) mode control. Connecting to Ground, the mode is automatically switched between the Light Load mode control and PWM mode control. Fix this pin to the VOUTS pin or Ground. Do not change the mode control during operation. |
| 9 | SS | Pin for setting the soft start time of output voltage. The soft start time is 1 ms (Typ) when the SS pin is open. A ceramic capacitor connected to the SS pin makes the soft start time 1 ms or more. See page 32 for how to calculate the capacitance. |
| 10 | AVIN | Pin for supplying power to the control circuit. Connecting 0.1 μ F (Typ) ceramic capacitor is recommended. This pin is connected to PVIN. |
| 11, 12 | PVIN | Power supply pins for the output MOSFETs. Connecting 10 μF (Typ) ceramic capacitor is recommended. |
| 13 | EN | Enable pin. The device starts up when V_{EN} is set to 0.9 V (Min) or more. The device enters the shutdown mode with setting V_{EN} to 0.3 V (Max) or less. This pin must be properly terminated. |
| 14 | VOUTS | Pin for discharging output and detecting output voltage. Connect to output voltage node. |
| 15, 16 | PGND | Ground pins for the output stage of the switching regulator. |
| - | EXP-PAD | A backside heat dissipation pad. Connecting to the internal PCB Ground plane by using via provides excellent heat dissipation characteristics. |

Block Diagram



Description of Blocks

1. REG

This block generates the internal power supply.

2. EN

This is the enable block. When EN voltage (V_{EN}) is set to 0.9 V (Min) or more, the internal circuit is activated and the device starts operation. Shutdown is forced if V_{EN} is set to 0.3 V (Max) or less.

3. UVLO

This block is for under voltage lockout protection. The device shuts down when input voltage falls to 3.6 V (Typ) or less. The threshold voltage has a hysteresis of 200 mV (Typ).

4. VREF

This block generates the internal reference voltage.

5. TSD

This block is for thermal protection. The device is shut down when the junction temperature (Tj) reaches to 175 °C (Typ) or more. The device is automatically restored to normal operation with a hysteresis of 25 °C (Typ) when the Tj goes down.

6. Soft Start

This block slows down the rise of output voltage during start-up and controls the current, which allows the prevention of output voltage (V_{OUT}) overshoot and inrush current. The internal soft start time is 1 ms (Typ) when the SS pin is open. A capacitor connected to the SS pin makes the rising time 1 ms or more.

7. PGOOD

This block is for power good function. When the FB voltage (V_{FB}) is more than or equal to 95 % (Typ) of 0.8 V, the builtin open drain Nch MOSFET connected to the PGD pin is off, and the PGD pin becomes High impedance. When V_{FB} is less than or equal to 90 % (Typ) of 0.8 V, it turns on the built-in open drain Nch MOSFET and the PGD pin is pulled down with 100 Ω (Typ).

8. Control Logic + DRV

This block controls switching operation and various protection functions.

9. OVP

This block is for output over voltage protection. When V_{FB} is more than or equal to 120 % (Typ) of 0.8 V, the output MOSFETs are off. After V_{FB} is less than or equal to 115 % (Typ) of 0.8 V, the output MOSFETs are returned to normal operation condition. In addition, when VOUTS voltage (V_{VOUTS}) reaches 5.95 V (Typ) or more, the output MOSFETs are off. After V_{VOUTS} falls 5.65 V (Typ) or less, the output MOSFETs are returned to normal operation condition. If the condition of the over voltage protection is continued for 20 µs (Typ), the output MOSFETs are latched to off.

10. HOCP

This block is for over current protection of the High-Side FET. When the current that flows through the High-Side FET reaches the value of over current limit, it turns off the High-Side FET and turns on the Low-Side FET.

11. LOCP

This block is for over current protection of the Low-Side FET. While the current that flows through the Low-Side FET over the value of over current limit, the condition that being turned on the Low-Side FET is continued.

12. SCP

This block is for short circuit protection. After soft start is completed and in condition where V_{FB} is less than or equal to 90 % (Typ) of 0.8 V, this block counts the number of times of which current flowing in the High-Side FET or the Low-Side FET reaches over current limit. When 256 times is counted, the device is shut down for 15 ms (Typ) and re-operates. Counting is reset when V_{FB} is more than or equal to 95 % (Typ) of 0.8V, or IC re-operates by EN, UVLO and SCP function.

13. Error Amplifier

The Error Amplifier adjusts Main Comparator input voltage to make the internal reference voltage equal to VFB.

14. Main Comparator

The Main Comparator compares the Error Amplifier output voltage and V_{FB} . When V_{FB} becomes lower than the Error Amplifier output voltage, the output turns High and reports to the On Time block that the output voltage has dropped below the control voltage.

15. On Time

This block generates On Time. The designed On Time is generated after the Main Comparator output turns High. The On Time is adjusted to control the frequency to be fixed even with I/O voltage is changed.

16. ZXCMP

The ZXCMP is a comparator that monitors the inductor current. When inductor current falls below 0 A (Typ) while the Low-Side FET is on, it turns the FET off.

Absolute Maximum Ratings (Ta = 25°C)

| Parameter | Symbol | Rating | Unit |
|------------------------------|---------------------------------------|---------------------------------|------|
| Input Voltage | V _{PVIN} , V _{AVIN} | -0.3 to +20 | V |
| EN Voltage | V _{EN} | -0.3 to V _{PVIN} + 0.3 | V |
| MODE Voltage | V _{MODE} | -0.3 to +7 | V |
| RESERVE Voltage | V _{RESERVE} | -0.3 to +7 | V |
| SS Voltage | V _{SS} | -0.3 to +20 | V |
| PGD Voltage | V _{PGD} | -0.3 to +7 | V |
| FB Voltage | V _{FB} | -0.3 to +7 | V |
| VOUTS Voltage | V _{VOUTS} | -0.3 to +7 | V |
| SW Voltage | V _{SW} | -0.3 to V _{PVIN} + 0.3 | V |
| Output Current | I _{OUT} | 3.5 | А |
| Maximum Junction Temperature | Tjmax | 150 | °C |
| Storage Temperature Range | Tstg | -55 to +150 | °C |

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

Thermal Resistance (Note 1)

| Parameter | Symbol | Thermal Res | Unit | |
|---|-----------------|-------------|---------------|------|
| Palameter | Symbol | 1s (Note 3) | 2s2p (Note 4) | Unit |
| VQFN016V3030 | i | | | |
| Junction to Ambient | θ _{JA} | 189.0 | 57.5 | °C/W |
| Junction to Top Characterization Parameter (Note 2) | Ψ_{JT} | 23 | 10 | °C/W |
| (Note 1) Based on JESD51-2A (Still-Air). | 1 1 | | 1 | |

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package. (Note 3) Using a PCB board based on JESD51-3.

| (Note 4) Using a PCB board based o | n JESD51-5, 7. | | | | | |
|--------------------------------------|----------------|----------------------|------------|----------------|--------------------|-----------|
| Layer Number of Measurement Board | Material | Board Size | | | | |
| Single | FR-4 | 114.3 mm x 76.2 mm x | x 1.57 mmt | | | |
| Тор | | | | | | |
| Copper Pattern | Thickness | | | | | |
| Footprints and Traces | 70 µm | | | | | |
| Layer Number of | Material | Board Size | | Thermal V | 'ia ^{(No} | te 5) |
| Measurement Board | Material | Doard Size | | Pitch | | Diameter |
| 4 Layers | FR-4 | 114.3 mm x 76.2 mm | x 1.6 mmt | 1.20 mm | ¢ | 0.30 mm |
| Тор | | 2 Internal Laye | ers | Botto | om | |
| | | | | | | |
| Copper Pattern | Thickness | Copper Pattern | Thickness | Copper Pattern | ۱ | Thickness |

(Note 5) This thermal via connects with the copper pattern of all layers.

Recommended Operating Conditions

| Parameter | Symbol | Min | Тур | Max | Unit |
|------------------------|---------------------------------------|--------------|-----|--------------|------|
| Input Voltage | V _{PVIN} , V _{AVIN} | 4.0 | - | 17 | V |
| Operating Temperature | Та | -40 | - | +85 (Note 1) | °C |
| Output Current | IOUT | 0 | - | 3 | Α |
| Output Voltage Setting | V _{RANGE} | 0.9 (Note 2) | - | 5.25 | V |

(Note 1) Tj must be lower than 150°C under actual operating environment. Life time is derated at junction temperature greater than 125 °C. (Note 2) Use under the condition of the output voltage (V_{OUT}) \geq input voltage (V_{IV}) × 0.125.

Electrical Characteristics (Unless otherwise specified Ta = 25 °C, V_{PVIN} = V_{AVIN} = 12 V, V_{EN} = 5 V, V_{MODE} = GND)

| Parameter | Symbol | Min | Тур | Max | Unit | Conditions |
|--|--------------------|-------|-------|--------------------|------|---|
| Power Supply (AVIN) | | | | | | |
| Shutdown Current | I _{SDN} | - | 3 | 10 | μA | $V_{EN} = 0 V$ |
| Operating Quiescent Current | I _{CC} | - | 20 | 40 | μA | I _{OUT} = 0 mA No switching |
| UVLO Detection Threshold Voltage | V _{UVLO} | 3.4 | 3.6 | 3.8 | V | V _{IN} falling |
| UVLO Hysteresis Voltage | VUVLOHYS | - | 200 | - | mV | |
| Enable | | | | | | |
| EN Input High Level Voltage | V _{ENH} | 0.9 | - | VAVIN | V | |
| EN Input Low Level Voltage | V _{ENL} | GND | - | 0.3 | V | |
| EN Input Current | I _{EN} | - | - | 10 | μA | |
| Reference Voltage, Error Amplifier, So | oft Start | | 1 | 1 | | |
| FB threshold Voltage | V _{FBTH} | 0.792 | 0.800 | 0.808 | V | |
| FB Input Current | I _{FB} | - | 1 | 100 | nA | V _{FB} = 0.8 V |
| Soft Start Charge Current | I _{SS} | 2.3 | 2.5 | 2.7 | μA | |
| Internal Soft Start Time | t _{SS} | 0.4 | 1 | 1.8 | ms | |
| Control | 11 | | 1 | | | |
| MODE Input High Level Voltage | V _{MODEH} | 0.9 | - | V _{VOUTS} | V | |
| MODE Input Low Level Voltage | V _{MODEL} | GND | - | 0.3 | V | |
| On Time | t _{ONT} | - | 333 | - | ns | V _{OUT} = 5.0 V |
| Power Good | -1 | | 1 | | | |
| Power Good Rising Threshold Voltage | V _{PGDR} | 92 | 95 | 98 | % | V _{FB} rising, V _{PGDR} = V _{FB} / V _{FBTH} x 100 |
| Power Good Falling Threshold Voltage | V _{PGDF} | 87 | 90 | 93 | % | V_{FB} falling, $V_{PGDF} = V_{FB} / V_{FBTH} \times 100$ |
| PGD Output Leakage Current | I _{LKPGD} | - | 0 | 800 | nA | $V_{PGD} = 5 V$ |
| PGD MOSFET ON Resistance | R _{PGD} | - | 100 | 200 | Ω | |
| PGD Low Level Voltage | V _{PGDL} | - | 0.2 | 0.4 | V | $I_{PGD} = 2 \text{ mA}$ |
| SW (MOSFET) | | | | | | |
| High-Side FET ON Resistance | R _{ONH} | - | 110 | 220 | mΩ | |
| Low-Side FET ON Resistance | R _{ONL} | - | 50 | 100 | mΩ | |
| High-Side Output Leakage Current | I _{LKH} | - | 0 | 10 | μA | No switching |
| Low-Side Output Leakage Current | I _{LKL} | - | 0 | 10 | μA | No switching |
| Protection | | | | | | |
| Output OVP Detection Voltage | V _{OVPH} | 115 | 120 | 125 | % | V_{FB} rising, $V_{OVPH} = V_{FB} / V_{FBTH} x 100$ |
| Output OVP Release Voltage | V _{OPVL} | 110 | 115 | 120 | % | V _{FB} falling, V _{OVPL} = V _{FB} / V _{FBTH} x 100 |
| Low-Side FET Over Current Detection Current ^(Note 3) | I _{LOCP} | 3.1 | 3.8 | - | А | |

(Note 3) No tested on outgoing inspection.

Typical Performance Curves

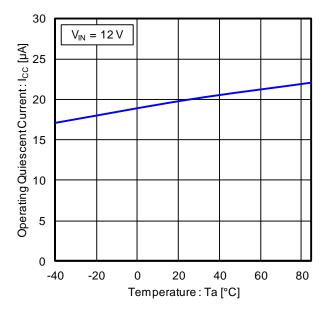


Figure 1. Operating Quiescent Current vs Temperature

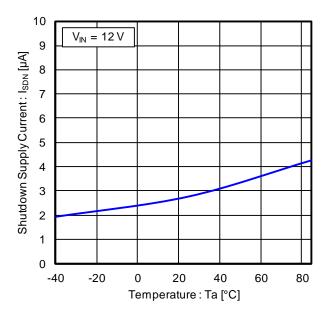


Figure 2. Shutdown Supply Current vs Temperature

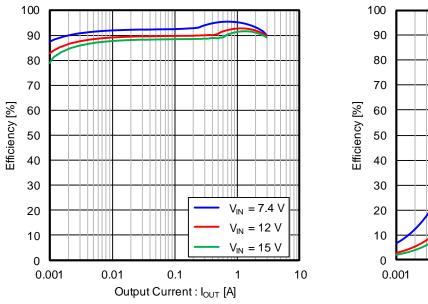


Figure 3. Efficiency vs Output Current ($V_{OUT} = 5 V$, L = 2.2 μ H, MODE = High)

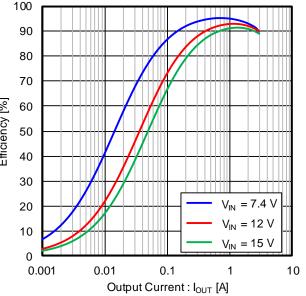


Figure 4. Efficiency vs Output Current ($V_{OUT} = 5 V$, L = 2.2 μ H, MODE = High)

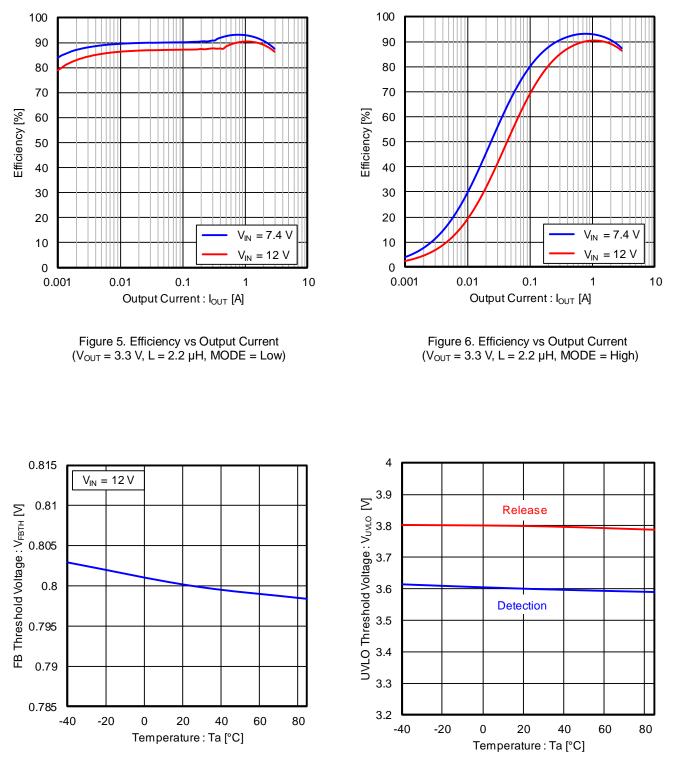


Figure 7. FB Threshold Voltage vs Temperature

Figure 8. UVLO Threshold Voltage vs Temperature

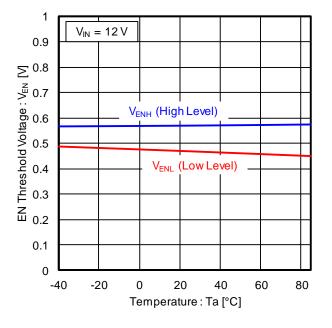


Figure 9. EN Threshold Voltage vs Temperature

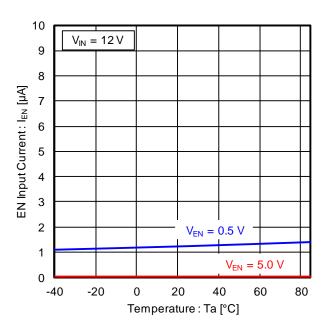


Figure 10. EN Input Current vs Temperature

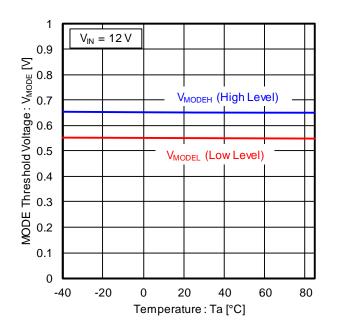


Figure 11. MODE Threshold Voltage vs Temperature

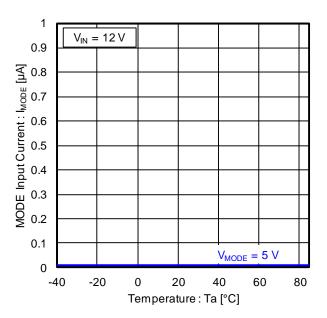


Figure 12. MODE Input Current vs Temperature

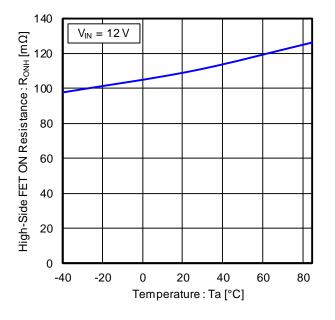


Figure 13. High-Side FET ON Resistance vs Temperature

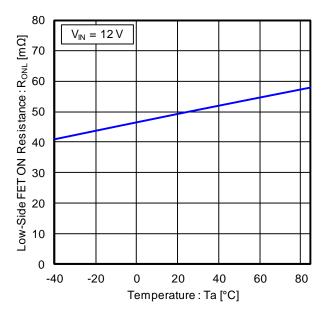


Figure 14. Low-Side FET ON Resistance vs Temperature

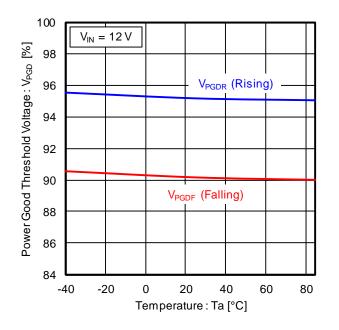


Figure 15. Power Good Threshold Voltage vs Temperature

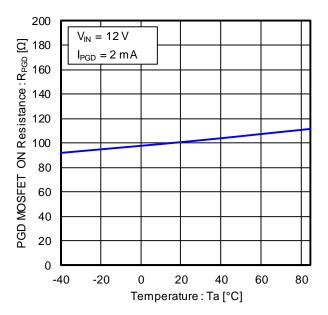


Figure 16. PGD MOSFET ON Resistance vs Temperature

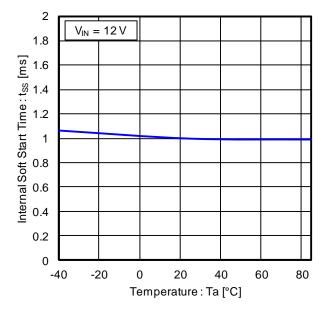


Figure 17. Internal Soft Start Time vs Temperature

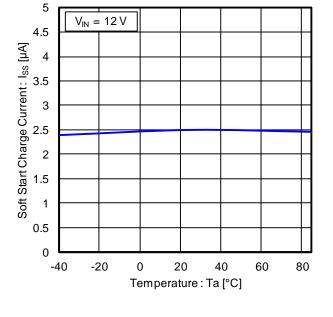


Figure 18. Soft Start Charge Current vs Temperature

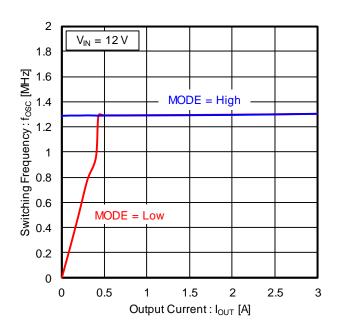


Figure 19. Switching Frequency vs Output Current (V_{IN} = 12 V, V_{OUT} = 5 V)

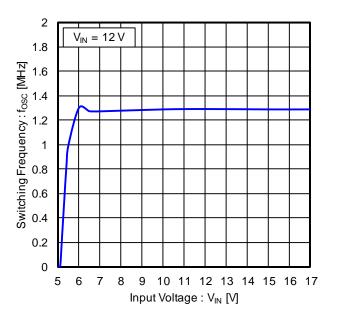
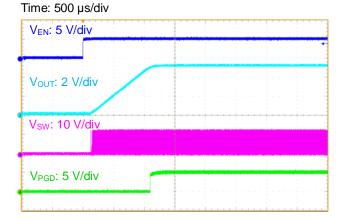
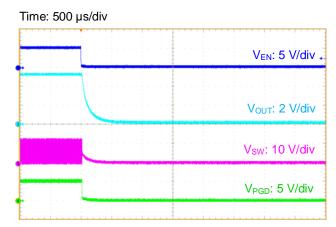


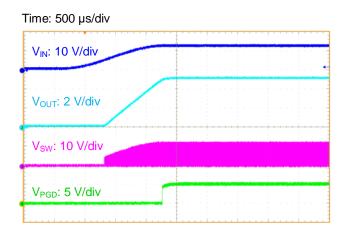
Figure 20. Switching Frequency vs Input Voltage ($V_{OUT} = 5.0 \text{ V}$, $I_{OUT} = 1 \text{ A}$, MODE = High)





| Figure 21. EN Start-up Waveform |
|--|
| $(V_{IN} = 12 \text{ V}, V_{OUT} = 5 \text{ V}, R_{LOAD} = 5 \Omega, \text{ MODE} = \text{Low})$ |

Figure 22. EN Shutdown Waveform (V_{IN} = 12 V, V_{OUT} = 5 V, R_{LOAD} = 5 \Omega, MODE = Low)

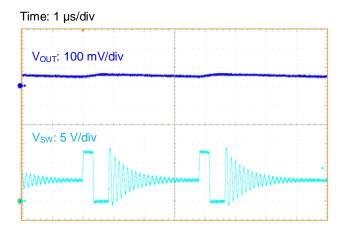


Time: 500 µs/div V_{IN}: 10 V/div V_{OUT}: 2 V/div V_{SW}: 10 V/div V_{PGD}: 5 V/div

Figure 23. VIN Start-up Waveform (V_{OUT} = 5 V, R_{LOAD} = 5 Ω , MODE = Low, V_{PVIN} = V_{AVIN} = V_{EN})

Figure 24. VIN Shutdown Waveform (V_{OUT} = 5 V, R_{LOAD} = 5 \Omega, MODE = Low, V_{PVIN} = V_{AVIN} = V_{EN})

Datasheet



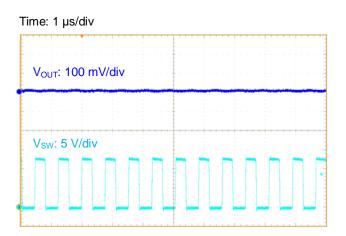


Figure 25. Switching Waveform (V_{IN} = 12 V, V_{OUT} = 5 V, I_{OUT} = 0.1 A, L = 2.2 μ H, C_{OUT} = 47 μ F, MODE = Low)

Figure 26. Switching Waveform (V_{IN} = 12 V, V_{OUT} = 5 V, I_{OUT} = 3.0 A, L = 2.2 μ H, C_{OUT} = 47 μ F, MODE = Low)

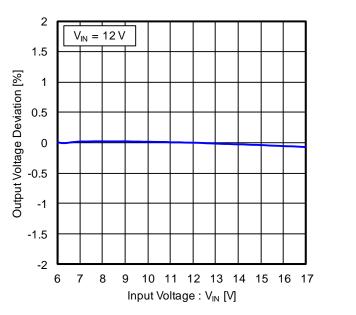


Figure 27. Line Regulation (V_{OUT} = 5 V, L = 2.2 μ H, I_{OUT} = 3.0 A)

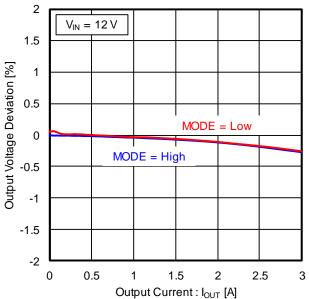


Figure 28. Load Regulation (V_{IN} = 12 V, V_{OUT} = 5 V, L = 2.2 $\mu H)$

Function Explanations

1. Basic Operation

(1) DC/DC Converter Operation

BD9D300MUV is a synchronous rectifying step-down switching regulator that has original on-time control method. When the MODE pin is connected to Ground, it utilizes switching operation in Pulse Width Modulation (PWM) mode control for heavier load, and it operates in Light Load mode control at lighter load to improve efficiency. When the MODE pin is connected to the VOUTS pin, the device operates in PWM mode control regardless of the load.

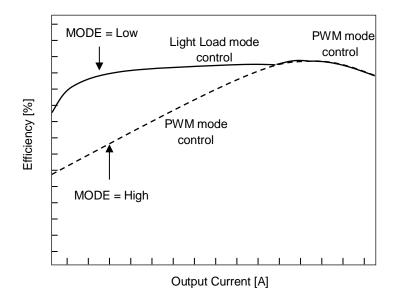
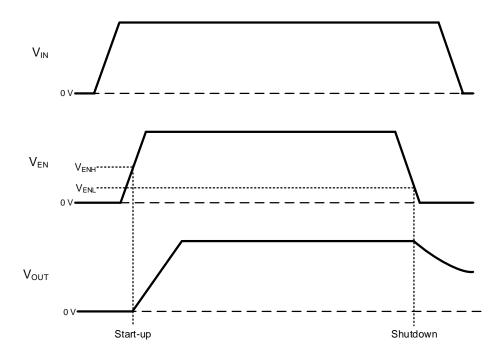
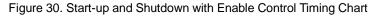


Figure 29. Efficiency Image between Light Load Mode Control and PWM Mode Control

(2) Enable Control

The start-up and shutdown can be controlled by the EN voltage (V_{EN}). When V_{EN} becomes 0.9 V (Min) or more, the internal circuit is activated and the device starts up. When V_{EN} becomes 0.3 V (Max) or less, the device is shut down. The start-up with V_{EN} must be at the same time of the input voltage (V_{IN}=V_{EN}) or after supplying V_{IN}.





1. Basic Operation – continued

(3) Soft Start

When V_{EN} goes high, soft start function operates and output voltage gradually rises. This soft start function can prevent overshoot of the output voltage and excessive inrush current. The soft start time (t_{SS}) is 1 ms (Typ) when the SS pin is left floating. A capacitor connected to the SS pin makes t_{SS} more than 1 ms. See <u>page 32</u> for how to set the soft start time. When Short Circuit Protection (SCP) is released, t_{SS} is 1 ms (Typ) regardless of a capacitor connected to the SS pin.

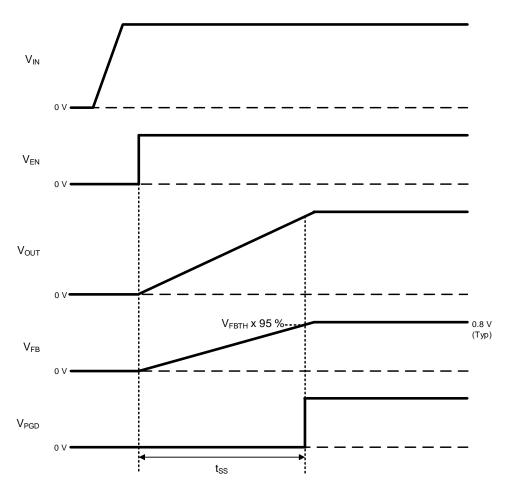


Figure 31. Soft Start Timing Chart

(4) Power Good

When the FB voltage (V_{FB}) is more than or equal to 95 % (Typ) of 0.8 V, the built-in open drain Nch MOSFET connected to the PGD pin is off, and the PGD pin becomes Hi-Z (High impedance). When V_{FB} is less than or equal to 90 % (Typ) of 0.8V, it turns on the built-in open drain Nch MOSFET turns on and the PGD pin is pulled down with 100 Ω (Typ). It is recommended to connect a pull-up resistor of 10 k Ω to 100 k Ω to the VOUTS pin.

| Table 1. PGD Output | | | | |
|-------------------------------|---|-----------------|--|--|
| State | Condition | PGD Output | | |
| Before Supply Input Voltage | V _{IN} < 1.6 V (Typ) | Hi-Z | | |
| Shutdown | $V_{EN} \le 0.3 V (Max)$ | Low (Pull-down) | | |
| Enable | 95 % (Typ) \leq V _{FB} / V _{FBTH} | Hi-Z | | |
| V _{EN} ≥ 0.9 V (Min) | $V_{FB} / V_{FBTH} \le 90 \% (Typ)$ | Low (Pull-down) | | |
| UVLO | 1.6 V (Typ) < V _{IN} ≤ 3.6 V (Typ) | Low (Pull-down) | | |
| TSD | Tj ≥ 175 °C (Typ) | Low (Pull-down) | | |
| OVP | 120 % (Typ) \leq V _{FB} / V _{FBTH} , 5.95 V (Typ) \leq V _{VOUTS} | Low (Pull-down) | | |
| SCP | Complete Soft Start V _{FB} / V _{FBTH} ≤ 90 % (Typ) OCP 256 counts | Low (Pull-down) | | |

(4) Power Good – continued

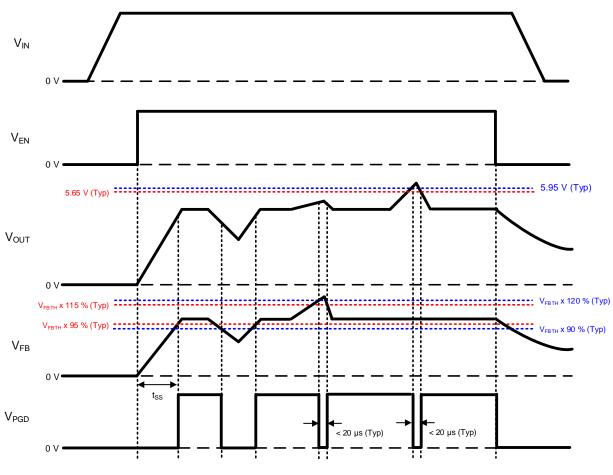


Figure 32. Power Good Timing Chart (Connecting a pull-up resistor to the PGD pin)

Function Explanations – continued

2. Protection

The protection circuits are intended for prevention of damage caused by unexpected accidents. Do not use the continuous protection.

(1) Over Current Protection (OCP) / Short Circuit Protection (SCP)

Over Current Protection (OCP) restricts the flowing current through the Low-Side FET or High-Side FET for every switching period. If the inductor current exceeds the Low-Side OCP $I_{LOCP} = 3.8 \text{ A}$ (Typ) while the Low-Side FET is on, the Low-Side FET remains on even with FB voltage (V_{FB}) falls to V_{FBTH} = 0.8 V (Typ) or less. If the inductor current becomes lower than I_{LOCP} , the High-Side FET is able to be turned on. When the inductor current is the High-Side OCP $I_{HOCP} = 4.8 \text{ A}$ (Typ) or more while the High-Side FET is on, it is turned off. Output voltage may decrease by changing frequency and duty due to OCP operation.

Short Circuit Protection (SCP) function is a Hiccup mode. When OCP operates 256 cycles while V_{FB} is less than or equal to 90 % (Typ) of 0.8V (V_{PGD} = Low), the device stops the switching operation for 15 ms (Typ). After 15 ms (Typ), the device restarts. SCP does not operate during the soft start even if the device is in the SCP condition. Do not exceed the maximum junction temperature (Tjmax = 150 °C) during OCP and SCP operation.

| V _{EN} | V _{FB} | Start-up | OCP | SCP |
|-----------------|----------------------------------|---------------------|---------|---------|
| | ≤ V _{FBTH} x 90 % (Typ) | During Soft Start | Enable | Disable |
| ≥ 0.9 V (Typ) | > V _{FBTH} х 95 % (Тур) | Complete Soft Start | Enable | Disable |
| | ≤ V _{FBTH} x 90 % (Typ) | | Enable | Enable |
| ≤ 0.3 V (Typ) | - | Shutdown | Disable | Disable |

| Table 2. | The Operating | Condition of | OCP and SCP |
|----------|---------------|--------------|-------------|
| | | | |

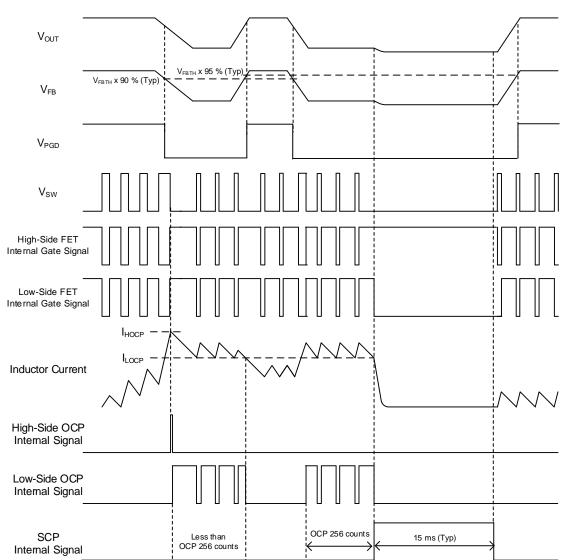


Figure 33. OCP and SCP Timing Chart

2. Protection - continued

(2) Under Voltage Lockout Protection (UVLO)

When input voltage (V_{IN}) falls to 3.6 V (Typ) or less, the device is shut down. When V_{IN} becomes 3.8 V (Typ) or more, the device starts up. The hysteresis is 200 mV (Typ).

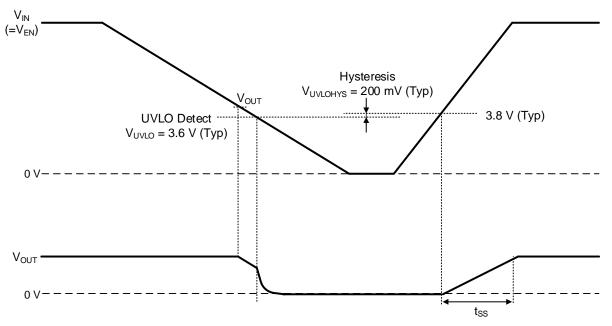


Figure 34. UVLO Timing Chart

(3) Thermal Shutdown Protection (TSD)

Thermal shutdown circuit prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating (Tjmax = 150 °C). However, if it continues exceeding the rating and the junction temperature Tj rises to 175 °C (Typ), the TSD circuit is activated and it turns the output MOSFETs off. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation. The TSD threshold has a hysteresis of 25 °C (Typ). Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings. Therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

(4) Over Voltage Protection (OVP)

When V_{FB} is more than or equal to 120 % (Typ) of 0.8 V, the output MOSFETs are off. After V_{FB} is less than or equal to 115 % (Typ) of 0.8 V, the output MOSFETs are returned to normal operation condition. In addition, when VOUTS voltage (V_{VOUTS}) reaches 5.95 V (Typ) or more, the output MOSFETs are off. After V_{VOUTS} falls 5.65 V (Typ) or less, the output MOSFETs are returned to normal operation of the over voltage protection is continued for 20 µs (Typ), the output MOSFETs are latched to off, and it re-operates by Enable control or UVLO function.

Application Examples

1. V_{IN} = 12 V / V_{OUT} = 5.0 V

| Parameter | Symbol | Specification Value |
|------------------------|---------------------|---------------------|
| Input Voltage | V _{IN} | 12 V |
| Output Voltage | Vout | 5.0 V |
| Switching Frequency | f _{osc} | 1.25 MHz (Typ) |
| Maximum Output Current | I _{OUTMAX} | 3 A |
| Operating Temperature | Та | 25 °C |

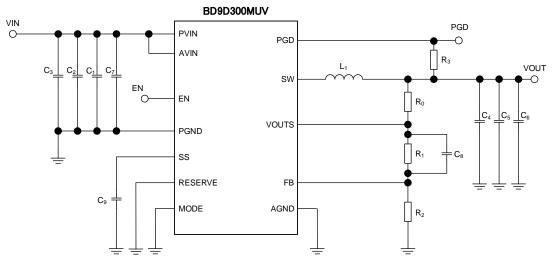


Figure 35. Application Circuit

| | Table 4. Recommended Component Values ($V_{IN} = 12 \text{ V / } V_{OUT} = 5.0 \text{ V}$) | | | | | | |
|-------------------------|--|-------------------|-----------|--------------|--|--|--|
| Part No. | Value | Part Name | Size (mm) | Manufacturer | | | |
| L ₁ | 2.2 μH | FDSD0518-H-2R2M | 5249 | Murata | | | |
| C1 (Note 2) | 10 µF (35 V / X5R) | GRM21BR6YA106ME43 | 2012 | Murata | | | |
| C ₂ | - | - | - | - | | | |
| C ₃ | - | - | - | - | | | |
| C4 (Note 3) | 47 µF (16 V / X5R) | GRM31CR61C476ME44 | 3216 | Murata | | | |
| C ₅ | - | - | - | - | | | |
| C ₆ | - | - | - | - | | | |
| C ₇ (Note 4) | 0.1 µF (35 V / X5R) | GRM033R6YA104ME14 | 0603 | Murata | | | |
| C ₈ | - | - | - | - | | | |
| C ₉ | - | - | - | - | | | |
| R ₁ | 270 kΩ (1 %, 1/16 W) | MCR01MZPF2703 | 1005 | ROHM | | | |
| R ₂ | 51 kΩ (1 %, 1/16 W) | MCR01MZPF5102 | 1005 | ROHM | | | |
| R ₃ | 100 kΩ (1 %, 1/16 W) | MCR01MZPF1003 | 1005 | ROHM | | | |
| R ₀ (Note 5) | Short | - | - | - | | | |

(Note 1) You agree that this is presented only as guidance for products use. Confirm on the actual equipment considering variations of the characteristics of the product and external components.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 2 µF.

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet.

(Note 4) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor as close as possible to the PVIN pin and the PGND pin if needed.

(Note 5) R₀ is an option used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit mode.

1. $V_{IN} = 12 \text{ V} / V_{OUT} = 5.0 \text{ V} - \text{continued}$

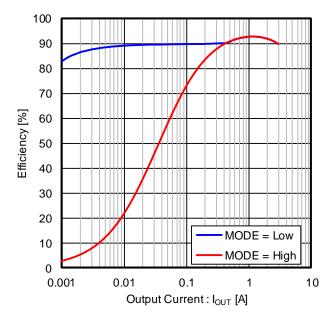


Figure 36. Efficiency vs Output Current

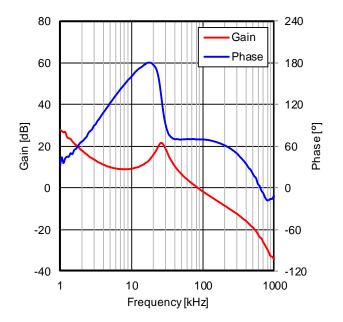
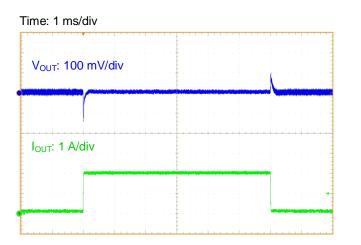
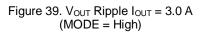


Figure 37. Frequency Characteristics $I_{OUT} = 2.0 \text{ A}$



Time: 1 μs/div V_{OUT}: 100 mV/div V_{SW}: 5 V/div

Figure 38. Load Transient Response $I_{OUT} = 0.1 \text{ A} - 2.0 \text{ A}$ (MODE = Low)



Application Examples – continued

2. V_{IN} = 7.4 V / V_{OUT} = 5.0 V

| Table 5. Specification of Application $(V_{IN} = 7.4 \text{ V} / V_{OUT} = 5.0 \text{ V})$ ParameterSymbolSpecification Value | | | | | | |
|---|---------------------|---------------------|--|--|--|--|
| T didifietei | Symbol | Specification value | | | | |
| Input Voltage | V _{IN} | 7.4 V | | | | |
| Output Voltage | Vout | 5.0 V | | | | |
| Switching Frequency | f _{osc} | 1.25 MHz (Typ) | | | | |
| Maximum Output Current | I _{OUTMAX} | 3 A | | | | |
| Operating Temperature | Та | 25 °C | | | | |

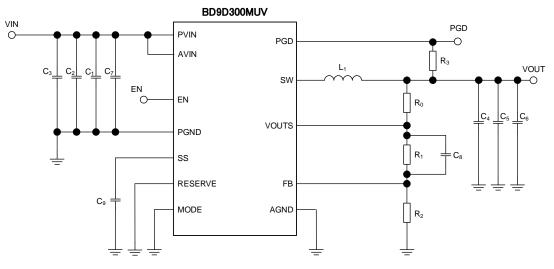


Figure 40. Application Circuit

| Table 6. Recommended Component Values $^{(Note 1)}$ (V _{IN} = 7.4 V / V _{OUT} = 5.0 V) | | | | | | |
|--|----------------------|-------------------|-----------|--------------|--|--|
| Part No. | Value | Part Name | Size (mm) | Manufacturer | | |
| L ₁ | 2.2 µH | FDSD0518-H-2R2M | 5249 | Murata | | |
| C1 (Note 2) | 10 µF (35 V / X5R) | GRM21BR6YA106ME43 | 2012 | Murata | | |
| C ₂ | - | - | - | - | | |
| C ₃ | - | - | - | - | | |
| C4 (Note 3) | 47 µF (16 V / X5R) | GRM31CR61C476ME44 | 3216 | Murata | | |
| C ₅ | - | - | - | - | | |
| C ₆ | - | - | - | - | | |
| C7 (Note 4) | 0.1 µF (35 V / X5R) | GRM033R6YA104ME14 | 0603 | Murata | | |
| C ₈ | - | - | - | - | | |
| C ₉ | - | - | - | - | | |
| R ₁ | 270 kΩ (1 %, 1/16 W) | MCR01MZPF2703 | 1005 | ROHM | | |
| R ₂ | 51 kΩ (1 %, 1/16 W) | MCR01MZPF5102 | 1005 | ROHM | | |
| R ₃ | 100 kΩ (1 %, 1/16 W) | MCR01MZPF1003 | 1005 | ROHM | | |
| R ₀ (Note 5) | Short | - | - | - | | |

| abla 6 | Recommended Co | mpopont Voluor | (Note 1) (\) | 7 1 1 / / | |
|---------|----------------|-----------------|--------------|-----------|-------------------|
| able b. | Recommended Co | inponent values | $(v_{IN} =$ | = 1.4 V / | $v_{OUT} = 5.0 v$ |

(Note 1) You agree that this is presented only as guidance for products use. Confirm on the actual equipment considering variations of the characteristics of the product and external components.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 2 µF.

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet.

(Note 4) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor as close as possible to the PVIN pin and the PGND pin if needed.

(Note 5) R₀ is an option used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit mode.

2. $V_{IN} = 7.4 \text{ V} / V_{OUT} = 5.0 \text{ V} - \text{continued}$

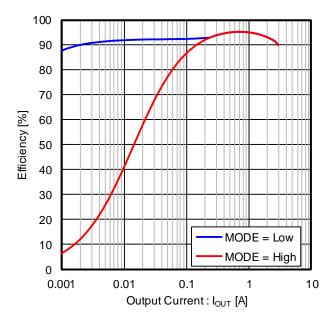


Figure 41. Efficiency vs Output Current

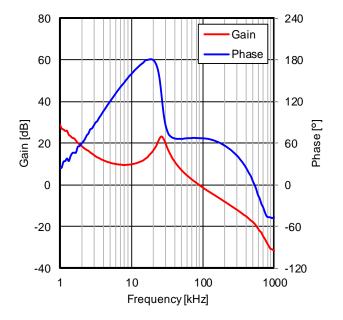
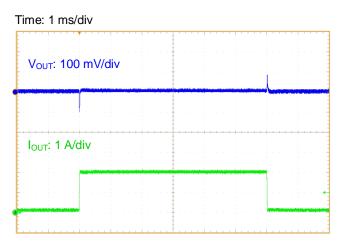
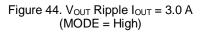


Figure 42. Frequency Characteristics $I_{OUT} = 2.0 \text{ A}$



Time: 1 µs/div

Figure 43. Load Transient Response $I_{OUT} = 0.1 \text{ A} - 2.0 \text{ A}$ (MODE = Low)



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Application Examples – continued

3. V_{IN} = 12 V / V_{OUT} = 3.3 V

| Parameter | Symbol | Specification Value |
|------------------------|------------------|---------------------|
| Input Voltage | V _{IN} | 12 V |
| Output Voltage | Vout | 3.3 V |
| Switching Frequency | f _{osc} | 1.25 MHz (Typ) |
| Maximum Output Current | IOUTMAX | 3 A |
| Operating Temperature | Та | 25 °C |

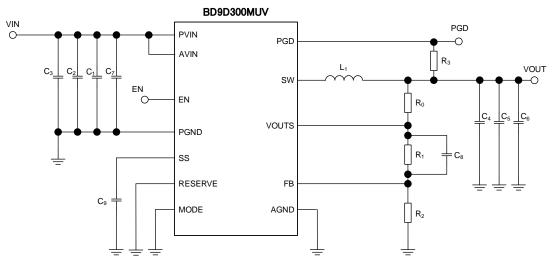


Figure 45. Application Circuit

| | Table 8. Recommended Component values ($V_{IN} = 12.7 / V_{OUT} = 3.3 V$) | | | | | | |
|-------------------------|---|-------------------|-----------|--------------|--|--|--|
| Part No. | Value | Part Name | Size (mm) | Manufacturer | | | |
| L ₁ | 2.2 μH | FDSD0518-H-2R2M | 5249 | Murata | | | |
| C1 (Note 2) | 10 µF (35 V / X5R) | GRM21BR6YA106ME43 | 2012 | Murata | | | |
| C ₂ | - | - | - | - | | | |
| C ₃ | - | - | - | - | | | |
| C4 (Note 3) | 47 µF (16 V / X5R) | GRM31CR61C476ME44 | 3216 | Murata | | | |
| C ₅ | - | - | - | - | | | |
| C ₆ | - | - | - | - | | | |
| C ₇ (Note 4) | 0.1 µF (35 V / X5R) | GRM033R6YA104ME14 | 0603 | Murata | | | |
| C ₈ | - | - | - | - | | | |
| C ₉ | - | - | - | - | | | |
| R ₁ | 160 kΩ (1 %, 1/16 W) | MCR01MZPF1603 | 1005 | ROHM | | | |
| R ₂ | 51 kΩ (1 %, 1/16 W) | MCR01MZPF5102 | 1005 | ROHM | | | |
| R ₃ | 100 kΩ (1 %, 1/16 W) | MCR01MZPF1003 | 1005 | ROHM | | | |
| R ₀ (Note 5) | Short | - | - | - | | | |

Table 8. Recommended Component Values (Note 1) (VIN = 12 V / VOUT = 3.3 V)

(Note 1) You agree that this is presented only as guidance for products use. Confirm on the actual equipment considering variations of the characteristics of the product and external components.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 2 µF.

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet.

(Note 4) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor as close as possible to the PVIN pin and the PGND pin if needed.

(Note 5) R₀ is an option used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit mode.

3. $V_{IN} = 12 \text{ V} / V_{OUT} = 3.3 \text{ V} - \text{continued}$

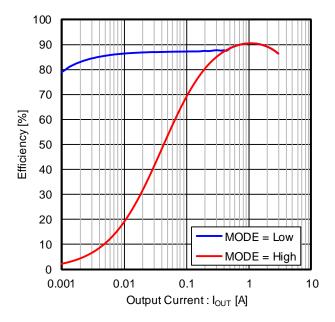


Figure 46. Efficiency vs Output Current

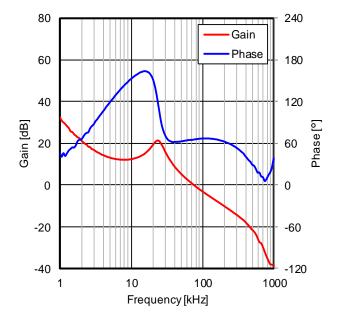
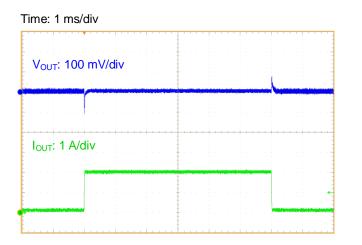
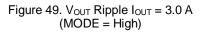


Figure 47. Frequency Characteristics $I_{OUT} = 2.0 \text{ A}$



Time: 1 µs/div

Figure 48. Load Transient Response $I_{OUT} = 0.1 \text{ A} - 2.0 \text{ A}$ (MODE = Low)



Application Examples – continued

4. $V_{IN} = 7.4 \text{ V} / V_{OUT} = 3.3 \text{ V}$

| Parameter | Symbol | Specification Value |
|------------------------|------------------|---------------------|
| Input Voltage | V _{IN} | 7.4 V |
| Output Voltage | Vout | 3.3 V |
| Switching Frequency | f _{osc} | 1.25 MHz (Typ) |
| Maximum Output Current | Ιουτμαχ | 3 A |
| Operating Temperature | Та | 25 °C |

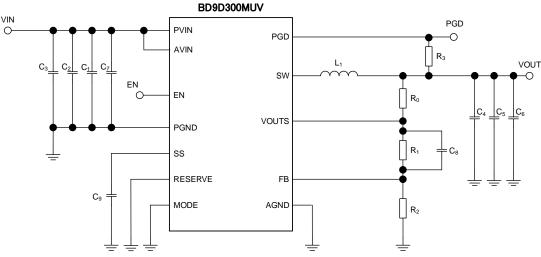


Figure 50. Application Circuit

| | Table 10. Recommended Component Values (Note 1) ($V_{IN} = 7.4 \text{ V} / V_{OUT} = 3.3 \text{ V}$) | | | | | | |
|-------------------------|--|-------------------|-----------|--------------|--|--|--|
| Part No. | Value | Part Name | Size (mm) | Manufacturer | | | |
| L ₁ | 2.2 μH | FDSD0518-H-2R2M | 5249 | Murata | | | |
| C1 (Note 2) | 10 µF (35 V / X5R) | GRM21BR6YA106ME43 | 2012 | Murata | | | |
| C ₂ | - | - | - | - | | | |
| C ₃ | - | - | - | - | | | |
| C ₄ (Note 3) | 47 µF (16 V / X5R) | GRM31CR61C476ME44 | 3216 | Murata | | | |
| C ₅ | - | - | - | - | | | |
| C ₆ | - | - | - | - | | | |
| C7 (Note 4) | 0.1 µF (35 V / X5R) | GRM033R6YA104ME14 | 0603 | Murata | | | |
| C ₈ | - | - | - | - | | | |
| C ₉ | - | - | - | - | | | |
| R ₁ | 160 kΩ (1 %, 1/16 W) | MCR01MZPF1603 | 1005 | ROHM | | | |
| R ₂ | 51 kΩ (1 %, 1/16 W) | MCR01MZPF5102 | 1005 | ROHM | | | |
| R ₃ | 100 kΩ (1 %, 1/16 W) | MCR01MZPF1003 | 1005 | ROHM | | | |
| R ₀ (Note 5) | Short | - | - | - | | | |

| | | | (Note 1) () (| | 0 0 1 0 |
|---------|--------------------|---------------|-----------------------------------|----------------------------|----------|
| able 10 | . Recommended Corr | ponent Values | $(V_{IN} = 1)$ (V _{IN} = | 7.4 V / V _{OUT} = | = 3.3 V) |

(Note 1) You agree that this is presented only as guidance for products use. Confirm on the actual equipment considering variations of the characteristics of the product and external components.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 2 µF.

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet.

(Note 4) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor as close as possible to the PVIN pin and the PGND pin if needed.

(Note 5) R₀ is an option used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit mode.

4. $V_{IN} = 7.4 \text{ V} / V_{OUT} = 3.3 \text{ V} - \text{continued}$

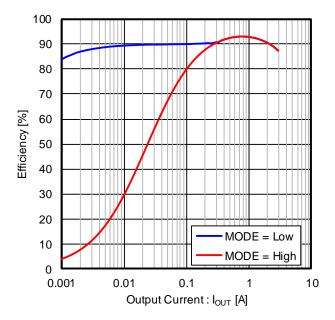


Figure 51. Efficiency vs Output Current

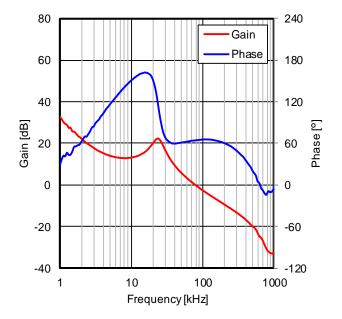
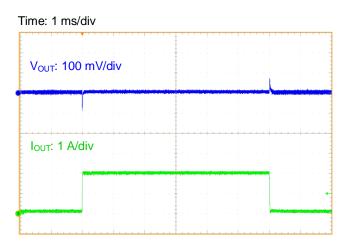
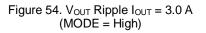


Figure 52. Frequency Characteristics $I_{OUT} = 2.0 \text{ A}$



Time: 1 μs/div V_{OUT}: 100 mV/div V_{SW}: 5 V/div

Figure 53. Load Transient Response $I_{OUT} = 0.1 \text{ A} - 2.0 \text{ A}$ (MODE = Low)



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Application Examples – continued

т.

5. V_{IN} = 7.4 V / V_{OUT} = 1.8 V

| Table 11. Specification of Application ($V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.8 \text{ V}$) | | | | | |
|---|------------------|---------------------|--|--|--|
| Parameter | Symbol | Specification Value | | | |
| Input Voltage | V _{IN} | 7.4 V | | | |
| Output Voltage | Vout | 1.8 V | | | |
| Switching Frequency | f _{osc} | 1.25 MHz (Typ) | | | |
| Maximum Output Current | Ioutmax | 3 A | | | |
| Operating Temperature | Та | 25 °C | | | |

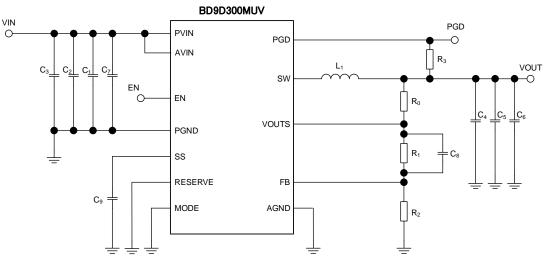


Figure 55. Application Circuit

| | Table 12. Recommended Component Values ($VOUP$) ($V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.8 \text{ V}$) | | | | | | |
|-------------------------|--|-------------------|-----------|--------------|--|--|--|
| Part No. | Value | Part Name | Size (mm) | Manufacturer | | | |
| L ₁ | 1.5 µH | FDSD0518-H-1R5M | 5249 | Murata | | | |
| C1 (Note 2) | 10 µF (35 V / X5R) | GRM21BR6YA106ME43 | 2012 | Murata | | | |
| C ₂ | - | - | - | - | | | |
| C ₃ | - | - | - | - | | | |
| C4 (Note 3) | 47 µF (16 V / X5R) | GRM31CR61C476ME44 | 3216 | Murata | | | |
| C ₅ | - | - | - | - | | | |
| C ₆ | - | - | - | - | | | |
| C7 (Note 4) | 0.1 µF (35 V / X5R) | GRM033R6YA104ME14 | 0603 | Murata | | | |
| C ₈ | - | - | - | - | | | |
| C ₉ | - | - | - | - | | | |
| R ₁ | 150 kΩ (1 %, 1/16 W) | MCR01MZPF1503 | 1005 | ROHM | | | |
| R ₂ | 120 kΩ (1 %, 1/16 W) | MCR01MZPF1203 | 1005 | ROHM | | | |
| R ₃ | 100 kΩ (1 %, 1/16 W) | MCR01MZPF1003 | 1005 | ROHM | | | |
| R ₀ (Note 5) | Short | - | - | - | | | |

| able | 12. 1 | Recommended | Component | Values | (Note 1) | VIN = | 7.4 V | / Vout = | 1.8 V) |
|------|-------|-------------|-----------|--------|----------|-------|---------------------|----------|--------|
| abic | 12.1 | Recommended | Component | values | · · · · | VIN - | 1. . v / | V001 - | 1.0 V) |

(Note 1) You agree that this is presented only as guidance for products use. Confirm on the actual equipment considering variations of the characteristics of the product and external components.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 2 µF.

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet.

(Note 4) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor as close as possible to the PVIN pin and the PGND pin if needed.

(Note 5) R₀ is an option used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit mode.

5. $V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.8 \text{ V} - \text{continued}$

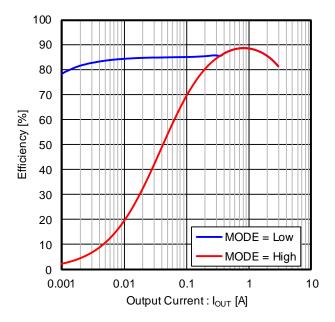


Figure 56. Efficiency vs Output Current

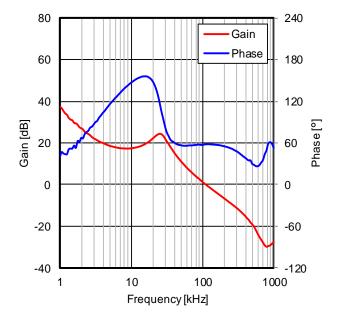
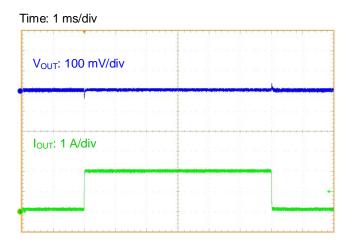


Figure 57. Frequency Characteristics $I_{OUT} = 2.0 \text{ A}$



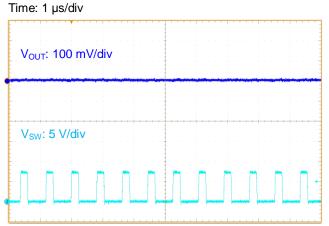


Figure 58. Load Transient Response $I_{OUT} = 0.1 \text{ A} - 2.0 \text{ A}$ (MODE = Low)

Figure 59. V_{OUT} Ripple I_{OUT} = 3.0 A (MODE = High)

Application Examples – continued

Τ/

6. $V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.2 \text{ V}$

| Table 13. Specification of Application ($V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.2 \text{ V}$) | | | |
|---|------------------|---------------------|--|
| Parameter | Symbol | Specification Value | |
| Input Voltage | V _{IN} | 7.4 V | |
| Output Voltage | Vout | 1.2 V | |
| Switching Frequency | f _{osc} | 1.25 MHz (Typ) | |
| Maximum Output Current | Ιουτμαχ | 3 A | |
| Operating Temperature | Та | 25 °C | |

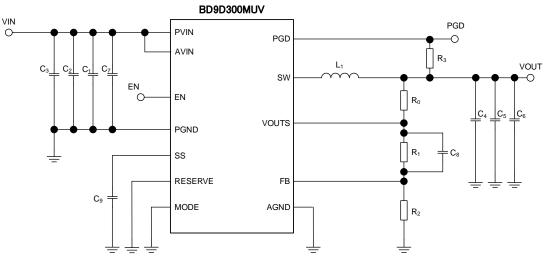


Figure 60. Application Circuit

| Table 14. Recommended Component Values ($VOIe^{-1}$) ($V_{IN} = 7.4$ V / $V_{OUT} = 1.2$ V) | | | | |
|--|----------------------|-------------------|-----------|--------------|
| Part No. | Value | Part Name | Size (mm) | Manufacturer |
| L ₁ | 1.0 µH | FDSD0518-H-1R0M | 5249 | Murata |
| C1 (Note 2) | 10 µF (35 V / X5R) | GRM21BR6YA106ME43 | 2012 | Murata |
| C ₂ | - | - | - | - |
| C ₃ | - | - | - | - |
| C4 (Note 3) | 47 µF (16 V / X5R) | GRM31CR61C476ME44 | 3216 | Murata |
| C ₅ | - | - | - | - |
| C ₆ | - | - | - | - |
| C7 (Note 4) | 0.1 µF (35 V / X5R) | GRM033R6YA104ME14 | 0603 | Murata |
| C ₈ | - | - | - | - |
| C ₉ | - | - | - | - |
| R ₁ | 150 kΩ (1 %, 1/16 W) | MCR01MZPF1503 | 1005 | ROHM |
| R ₂ | 300 kΩ (1 %, 1/16 W) | MCR01MZPF3003 | 1005 | ROHM |
| R ₃ | 100 kΩ (1 %, 1/16 W) | MCR01MZPF1003 | 1005 | ROHM |
| R ₀ (Note 5) | Short | - | - | - |

| able 14. Recommended Com | ponent Values (Note 1) | $(V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.2 \text{ V})$ |
|--------------------------|------------------------|--|
| | | $(V_{IN} = 7.1 V, V_{OUI} = 1.2 V)$ |

(Note 1) You agree that this is presented only as guidance for products use. Confirm on the actual equipment considering variations of the characteristics of the product and external components.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 2 µF.

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet.

(Note 4) In order to reduce the influence of high frequency noise, connect a 0.1 µF ceramic capacitor as close as possible to the PVIN pin and the PGND pin if needed.

(Note 5) R₀ is an option used for feedback's frequency response measurement. By inserting a resistor at R₀, it is possible to measure the frequency response (phase margin) using a FRA. However, the resistor will not be used in actual application, use this resistor pattern in short-circuit mode.

6. $V_{IN} = 7.4 \text{ V} / V_{OUT} = 1.2 \text{ V} - \text{continued}$

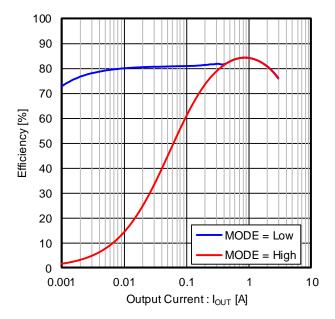


Figure 61. Efficiency vs Output Current

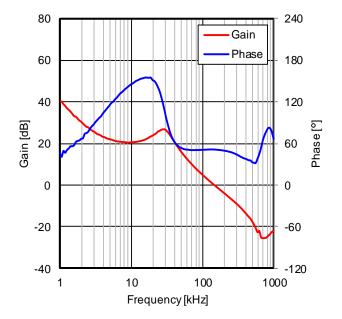
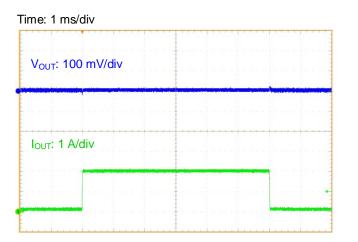


Figure 62. Frequency Characteristics $I_{OUT} = 2.0 \text{ A}$



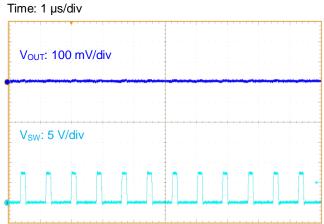
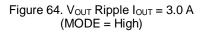


Figure 63. Load Transient Response $I_{OUT} = 0.1 \text{ A} - 2.0 \text{ A}$ (MODE = Low)



Selection of Components Externally Connected

Contact us if not use the recommended component values in Application Examples.

1. Output LC Filter

In order to supply a continuous current to the load, the DC/DC converter requires an LC filter for smoothing the output voltage.

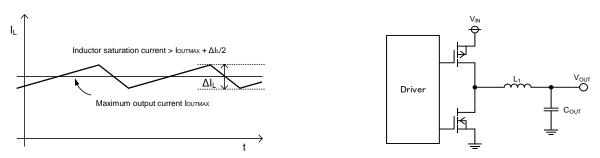


Figure 65. Waveform of current through inductor

Figure 66. Output LC filter circuit

For example, given that $V_{IN} = 12$ V, $V_{OUT} = 5.0$ V, $L_1 = 2.2 \mu$ H, and the switching frequency $f_{OSC} = 1.25$ MHz, the inductor ripple current ΔI_L can be calculated as below.

$$\Delta I_L = V_{OUT} \times (V_{IN} - V_{OUT}) \times \frac{1}{V_{IN} \times f_{OSC} \times L_1} = 1061 \text{ mA}$$

The inductance value of L₁ is recommended in the range between 1.0 μ H and 3.3 μ H. However, Δ I_L should be set 400 mA or more when using Light Load mode control by the MODE pin connecting to Ground.

The rated current of the inductor (Inductor saturation current) must be larger than the sum of the maximum output current I_{OUTMAX} and 1/2 of the inductor ripple current ΔI_L .

The output capacitor C_{OUT} affects the output ripple voltage characteristics. The capacitance value of C_{OUT} is recommended in the range between 22 μ F and 47 μ F for stability of the control loop. C_{OUT} must satisfy the required ripple voltage characteristics.

The output ripple voltage ΔV_{RPL} can be estimated by the following equation.

$$\Delta V_{RPL} = \Delta I_L \times \left(R_{ESR} + \frac{1}{8 \times C_{OUT} \times f_{OSC}} \right)$$
 [V]

Where:

 R_{ESR} is the Equivalent Series Resistance of the output capacitor.

For example, given that $C_{OUT} = 47 \ \mu\text{F}$, and $R_{ESR} = 3 \ m\Omega$, ΔV_{RPL} can be calculated as below.

$$\Delta V_{RPL} = 1061 \, mA \, \times \, \left(3 \, m\Omega \, + \, \frac{1}{8 \, \times \, 47 \, \mu F \, \times \, 1.25 \, MHz} \right) = 5.4 \, [mV]$$

The total capacitance C_{OUTMAX} connected to V_{OUT} needs to satisfy the value obtained by the following equation.

$$C_{OUTMAX} < \frac{t_{SSMIN}}{V_{OUT}} \times (3.1 + \frac{\Delta I_L}{2} - I_{OUTSS})$$
 [F]

where:

 t_{SSMIN} is the minimum soft start time.

 V_{OUT} is the output voltage.

 ΔI_L is the inductor current.

IOUTSS is the maximum output current during soft start.

For example, given that V_{IN} = 12 V, V_{OUT} = 5.0 V, L_1 = 2.2 μ H, f_{OSC} = 1.25 MHz (Typ), t_{SSMIN} = 0.4 ms (C_{SS} = OPEN), and I_{OUTSS} = 3 A, C_{OUTMAX} can be calculated as below.

$$C_{OUTMAX} < \frac{0.4 \text{ ms}}{5.0 \text{ V}} \times \left(3.1 + \frac{1061 \text{ mA}}{2} - 3.0 \text{ A}\right) = 50.4 \text{ [µF]}$$

If the total capacitance connected to V_{OUT} is larger than C_{OUTMAX} , over current protection may be activated by the inrush current at start-up and prevented to turn on the output. In addition, C_{OUT} affects the load transient response and stability of the control loop. Confirm it on the actual application.

Selection of Components Externally Connected – continued

2. Output Voltage Setting

The output voltage value can be set by the feedback resistance ratio. For stable operation, use feedback resistance R_1 of value from 100 k Ω to 300 k Ω .

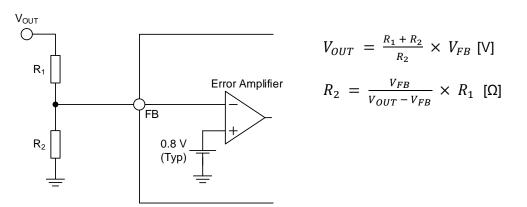


Figure 67. Feedback Resistor Circuit

3. Soft Start Capacitor (Soft Start Time Setting)

The soft start time t_{SS} depends on the value of the capacitor connected to the SS pin. t_{SS} is 1 ms (Typ) when the SS pin is left floating. The capacitor connected to the SS pin makes t_{SS} more than 1 ms. The t_{SS} and C_{SS} can be calculated using below equation. The C_{SS} should be set in the range between 3300 pF and 0.1 μ F.

$$t_{SS} = \frac{(C_{SS} \times V_{SS})}{I_{SS}}$$

Where:

 t_{SS} is the soft start time. C_{SS} is the capacitor connected to the SS pin. V_{SS} is the SS voltage finished soft start function. I_{SS} is the soft start current. 2.5 µA (Typ)

1.2 V (Typ) x 0.95 (Typ)

With C_{SS} = 0.01 $\mu\text{F},\,t_{\text{SS}}$ can be calculated as below.

$$t_{SS} = \frac{(0.01 \ \mu\text{F} \times 1.2 \ \text{V} \times 0.95)}{2.5 \ \mu\text{A}} = 4.56 \ \text{ms}$$

PCB Layout Design

PCB layout design for DC/DC converter power supply IC is as important as the circuit design. Appropriate layout can avoid various problems caused by power supply circuit. Figure 68-a to Figure 68-c show the current path in a buck converter circuit. The Loop1 in Figure 68-a is a current path when H-side switch is ON and L-side switch is OFF and the Loop2 in Figure 68-b is when H-side switch is OFF and L-side switch is ON. The thick line in Figure 68-c shows the difference between Loop1 and Loop2. The current in thick line changes sharply each time the switching element H-side and L-side switch change from OFF to ON, and vice versa. These sharp changes induce several harmonics in the waveform. Therefore, the loop area of thick line that is consisted by input capacitor and IC should be as small as possible to minimize noise. For more detail, refer to application note of switching regulator series "PCB Layout Techniques of Buck Converter".

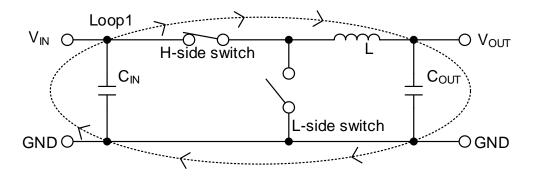


Figure 68-a. Current Path when H-side Switch = ON, L-side Switch = OFF

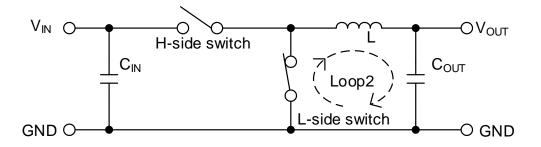


Figure 68-b. Current Path when H-side Switch = OFF, L-side Switch = ON

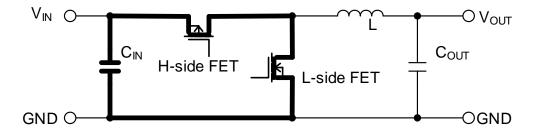
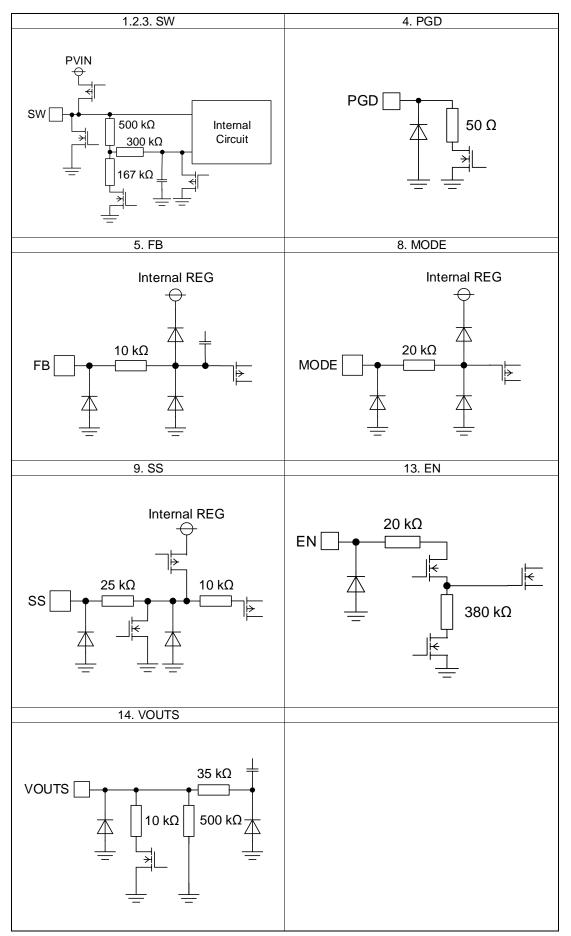


Figure 68-c. Difference of Current and Critical Area in Layout

I/O Equivalence Circuits



Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition. However, pins that drive inductive loads (e.g. motor driver outputs, DC-DC converter outputs) may inevitably go below ground due to back EMF or electromotive force. In such cases, the user should make sure that such voltages going below ground will not cause the IC and the system to malfunction by examining carefully all relevant factors and conditions such as motor characteristics, supply voltage, operating frequency and PCB wiring to name a few.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operation Notes – continued

10. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

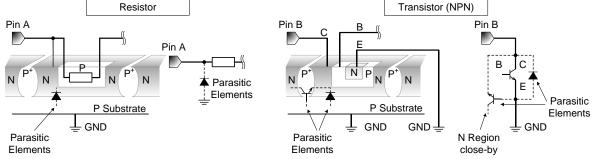


Figure 69. Example of Monolithic IC Structure

11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

12. Thermal Shutdown Circuit(TSD)

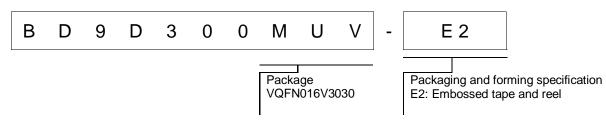
This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF power output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

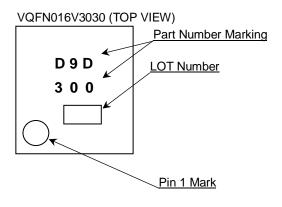
13. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

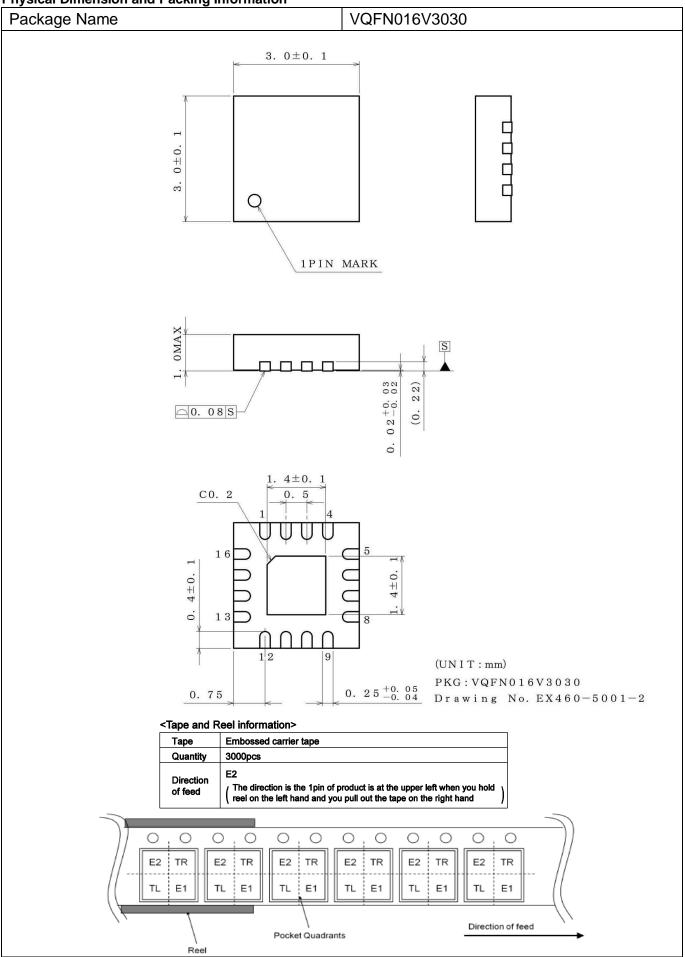
Ordering Information



Marking Diagram



Physical Dimension and Packing Information



Revision History

| Date | Revision | Changes |
|-------------|----------|-------------|
| 18.Mar.2019 | 001 | New Release |

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|---|
|---|

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 - [h] Use of the Products in places subject to dew condensation
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- 8. Confirm that operation temperature is within the specified range described in the product specification.
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